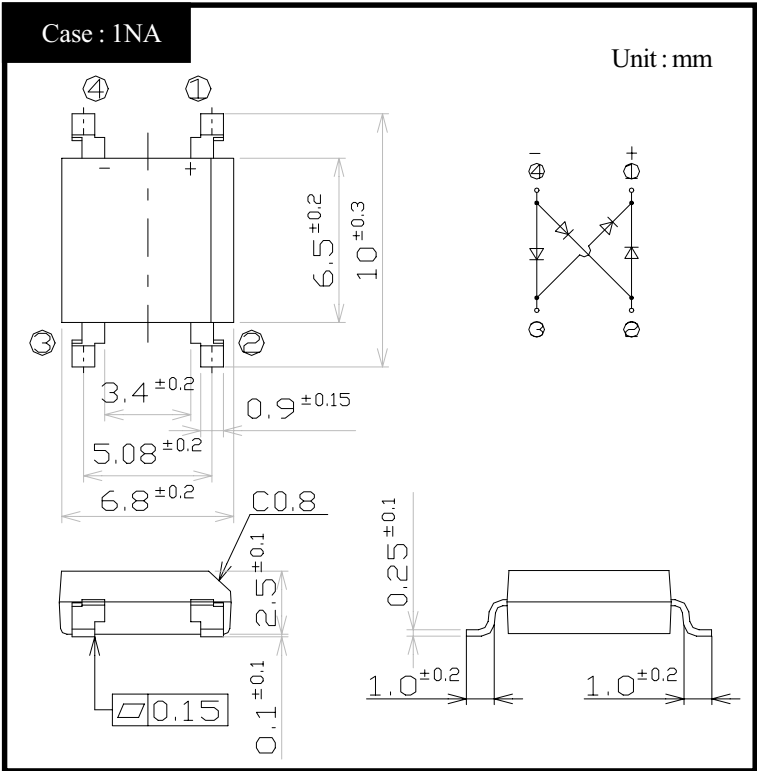


S1NBB80

800V 1A

OUTLINE DIMENSIONS



RATINGS

Absolute Maximum Ratings (If not specified Ta=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-40 to 150	°C
Operating Junction Temperature	Tj		150	°C
Maximum Reverse Voltage	VRM		800	V
Average Rectified Forward Current	Io	50Hz sine wave, R-load, Glass-epoxy substrate, Ta=26°C *1	1	A
	Io	50Hz sine wave, R-load, Glass-epoxy substrate, Ta=25°C *2	0.84	A
Peak Surge Forward Current	IFSM	50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=25°C	50	A
Current Squared Time	I²t	1ms≤t<10ms Tj=25°C	6	A²s

Electrical Characteristics (If not specified Ta=25°C)

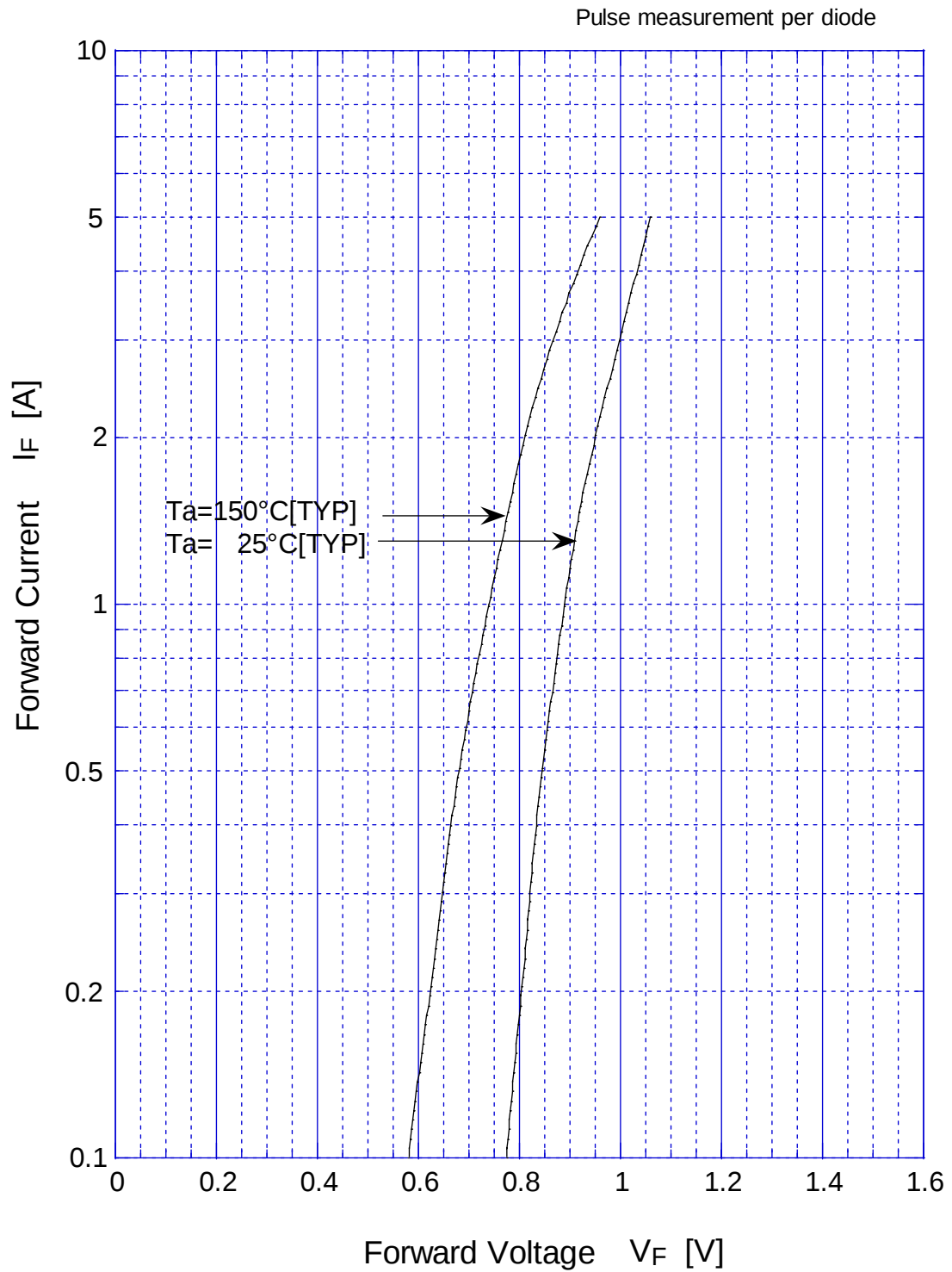
Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	VF	IF=0.5A, Pulse measurement, Rating of per diode	Max 1.05	V
Reverse Current	IR	VR=VRM, Pulse measurement, Rating of per diode	Max 10	μ A
Thermal Resistance	θjl	junction to lead	Max 15	°C/W
	θja	junction to ambient *1	Max 68	
	θja	junction to ambient *2	Max 84	

*1 : Glass epoxy substrate (pattern area : 324mm²)

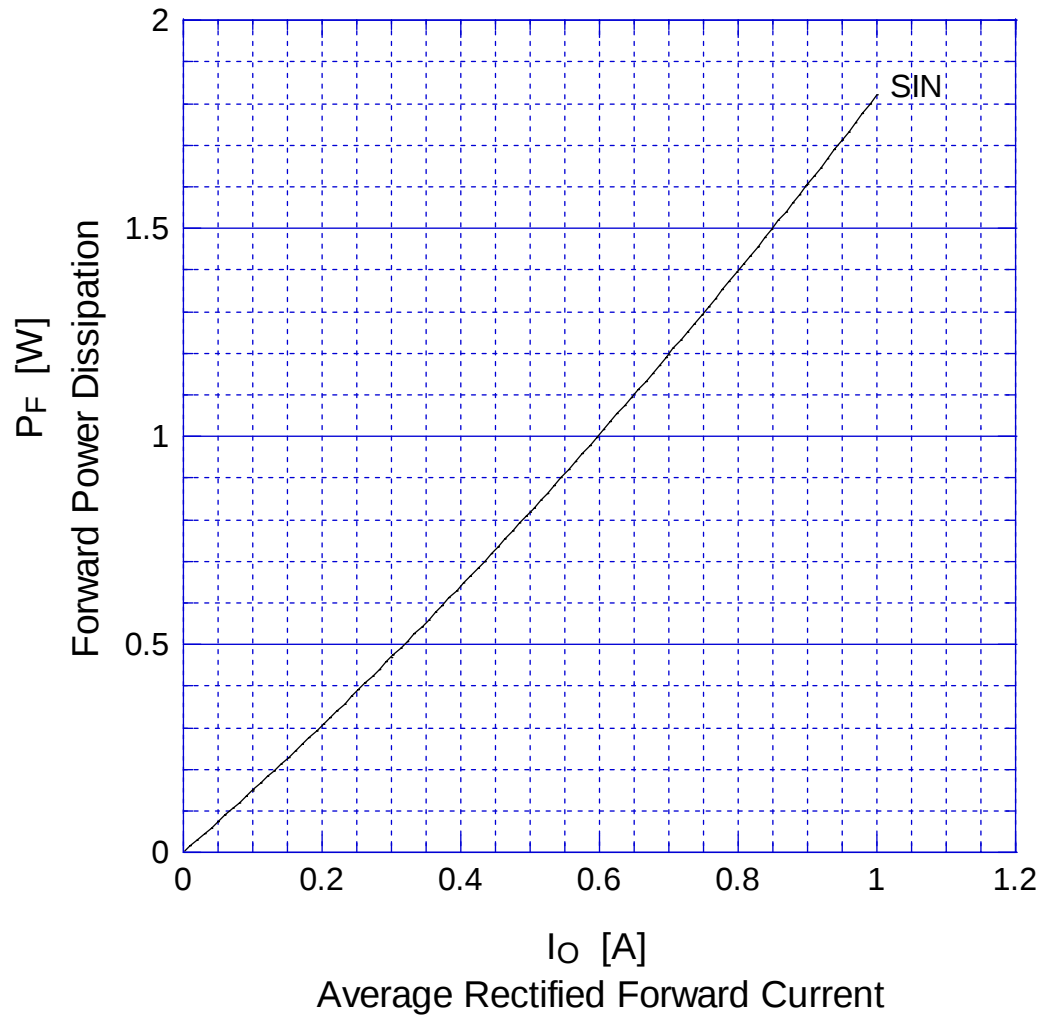
*2 : Glass epoxy substrate (pattern area : 101mm²)

S1NBB80

Forward Voltage



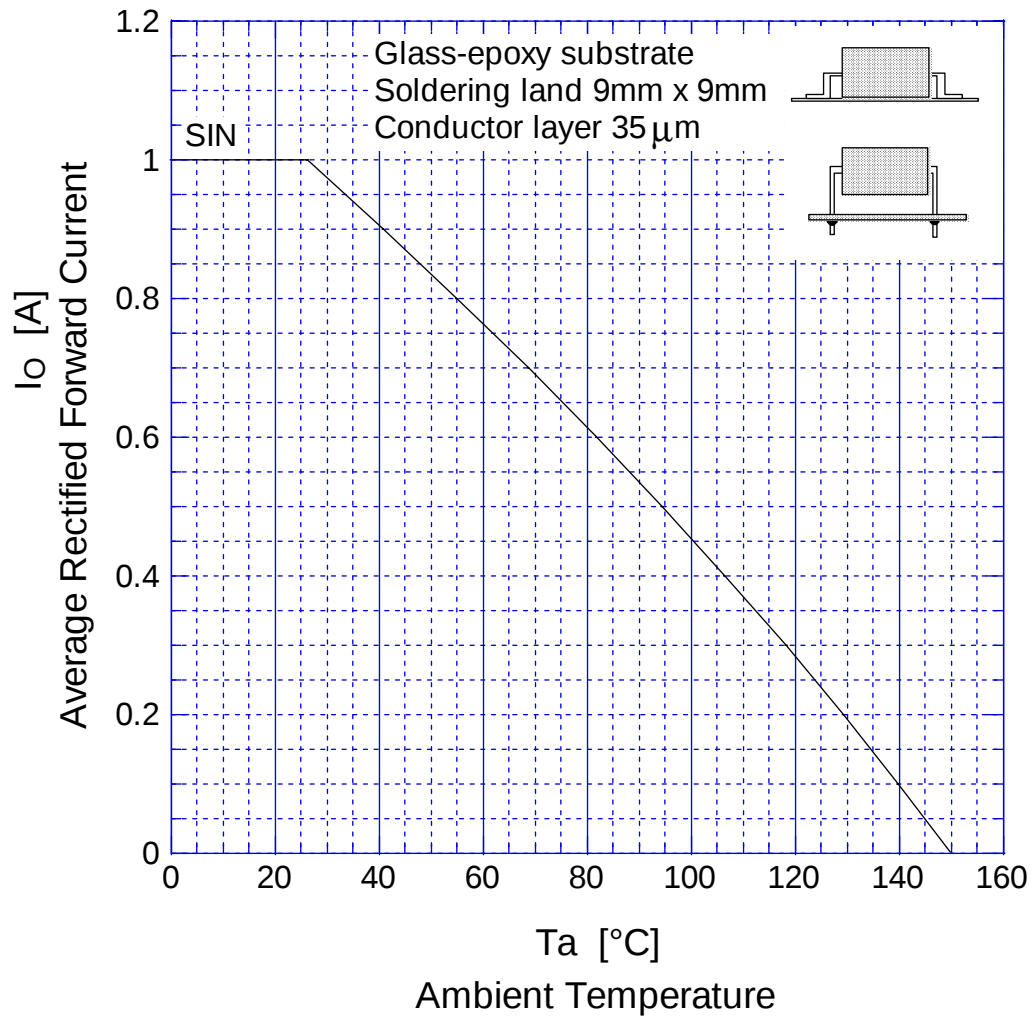
S1NBB80 Forward Power Dissipation



$T_j = 150^\circ\text{C}$

S1NBB80

Derating Curve



$$V_R = V_{RM}$$

S1NBB80 Peak Surge Forward Capability

